查询UPA2791GR-E2-AT供应商 捷多邦，专业PCB打样工厂，24小时加急出货

DATA SHEET

NEC

MOS FIELD EFFECT TRANSISTOR
μPA2791GR

SWITCHING
N- AND P-CHANNEL POWER MOS FET

DESCRIPTION

The μPA2791GR is N- and P-channel MOS Field Effect Transistors designed for switching application.

FEATURES

- Low on-state resistance

  N-channel $R_{DS(on)1}$ = 36.0 mΩ MAX. (V_{GS} = 10 V, I_D = 3.0 A)

  $R_{DS(on)2}$ = 50.0 mΩ MAX. (V_{GS} = 4.5 V, I_D = 3.0 A)

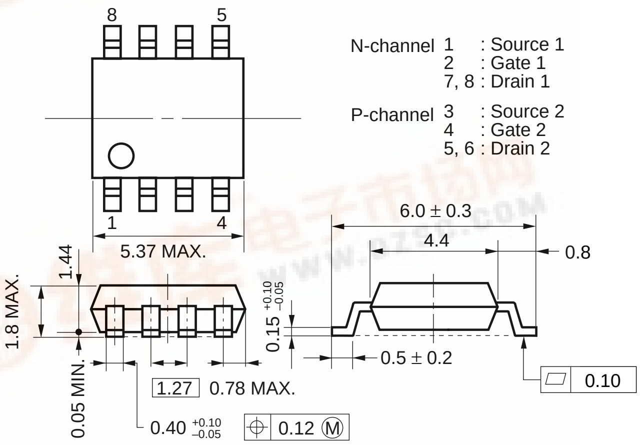
  P-channel $R_{DS(on)1}$ = 82 mΩ MAX. (V_{GS} = –10 V, I_D = –3.0 A)

  $R_{DS(on)2}$ = 110 mΩ MAX. (V_{GS} = –4.5 V, I_D = –3.0 A)
- Low gate charge

  N-channel Q_G = 10 nC TYP. (V_{GS} = 10 V)

  P-channel Q_G = 8.3 nC TYP. (V_{GS} = –10 V)
- Built-in gate protection diode
- Small and surface mount package (Power SOP8)

PACKAGE DRAWING (Unit: mm)

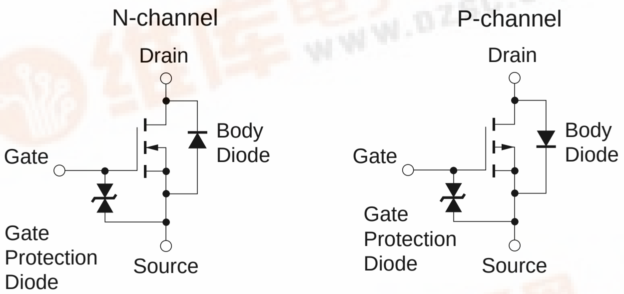


ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μPA2791GR-E1-AT Note	Pure Sn	Tape 2500 p/reel	Power SOP8
μPA2791GR-E2-AT Note			

Note Pb-free (This product does not contain Pb in the external electrode and other parts.)

EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge. V_{ESD} ± 600 V TYP. (C = 100 pF, R = 1.5 kΩ)

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The mark <R> shows major revised points.
The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C. All terminals are connected.)

	PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
	Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	30	–30	V
	Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	∓20	V
	Drain Current (DC) (T_C = 25°C) Note2	$I_{D(DC)}$	±5	∓5	A
	Drain Current (pulse) Note1	$I_{D(pulse)}$	±20	∓20	A
	Total Power Dissipation (1 unit) Note2	P_{T1}	1.7		W
	Total Power Dissipation (2 units) Note2	P_{T2}	2.0		W
	Channel Temperature	T_{ch}	150		°C
	Storage Temperature	T_{stg}	–55 to +150		°C
<R>	Single Avalanche Current Note3	I_{AS}	5	–5	A
<R>	Single Avalanche Energy Note3	E_{AS}	2.5		mJ

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on ceramic substrate of 2000 mm^2 x 1.6 mmt

<R> **3.** Starting T_{ch} = 25°C, V_{DD} = 1/2 x V_{DSS}, R_G = 25 Ω, L = 100 μH, V_{GS} = V_{GSS} → 0 V

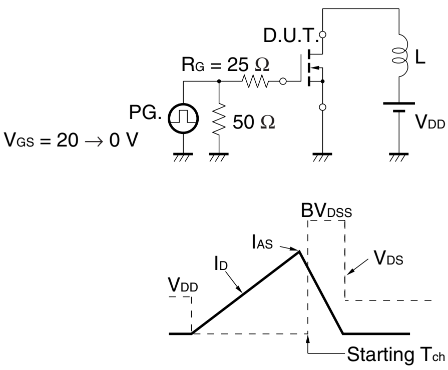
ELECTRICAL CHARACTERISTICS (T_A = 25°C. All terminals are connected.)

N-channel

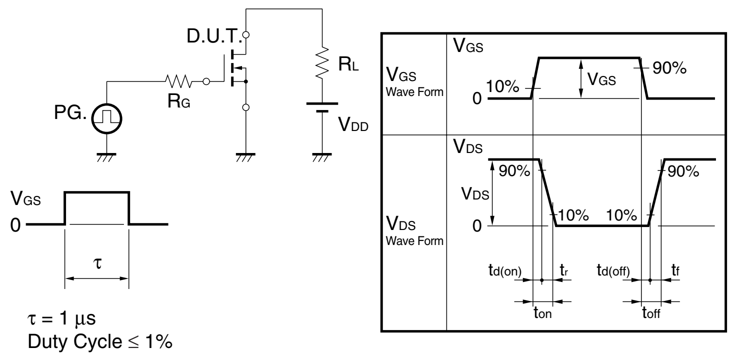
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V			±10	μA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1 mA	1.0		2.5	V
Forward Transfer Admittance Note	$\mid y_{fs} \mid$	V_{DS} = 10 V, I_D = 3 A	2.0			S
Drain to Source On-state Resistance Note	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 3.0 A		28.5	36.0	mΩ
	$R_{DS(on)2}$	V_{GS} = 4.5 V, I_D = 3.0 A		36.0	50.0	mΩ
Input Capacitance	C_{iss}	V_{DS} = 10 V,		400		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V,		80		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		50		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 15 V, I_D = 3 A,		7		ns
Rise Time	t_r	V_{GS} = 10 V,		4		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		21		ns
Fall Time	t_f			5		ns
Total Gate Charge	Q_G	I_D = 5 A,		10		nC
Gate to Source Charge	Q_{GS}	V_{DD} = 24 V,		1.5		nC
Gate to Drain Charge	Q_{GD}	V_{GS} = 10 V		2.7		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = 5 A, V_{GS} = 0 V		0.86		V
Reverse Recovery Time	t_{rr}	I_F = 5 A, V_{GS} = 0 V,		20		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 50 A/μs		16		nC

Note Pulsed

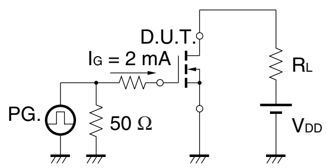
<R> **TEST CIRCUIT 1 AVALANCHE CAPABILITY**



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE

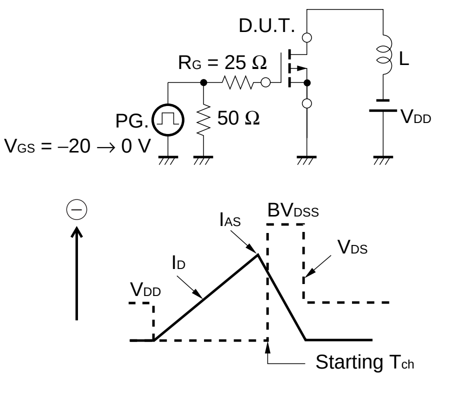


P-channel

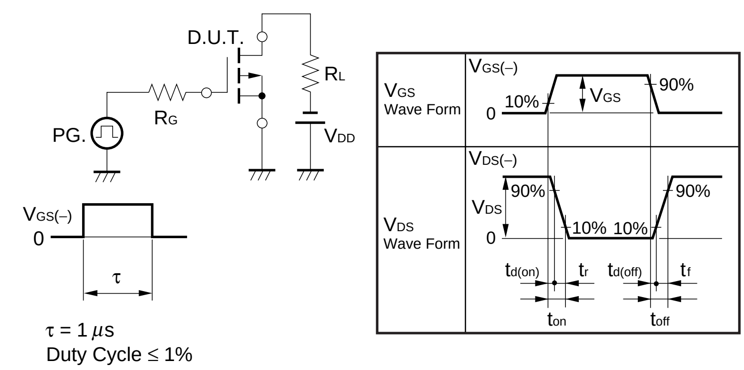
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –30 V, V_{GS} = 0 V			–10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ∓16 V, V_{DS} = 0 V			∓10	μA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = –10 V, I_D = –1 mA	–1.0		–2.5	V
Forward Transfer Admittance Note	| y_{fs} |	V_{DS} = –10 V, I_D = –3 A	1.0			S
Drain to Source On-state Resistance Note	$R_{DS(on)1}$	V_{GS} = –10 V, I_D = –3.0 A		63	82	mΩ
	$R_{DS(on)2}$	V_{GS} = –4.5 V, I_D = –3.0 A		79	110	mΩ
Input Capacitance	C_{iss}	V_{DS} = –10 V,		300		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V,		75		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		60		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = –15 V, I_D = –3 A,		8		ns
Rise Time	t_r	V_{GS} = –10 V,		14		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		50		ns
Fall Time	t_f			40		ns
Total Gate Charge	Q_G	I_D = –5 A,		8.3		nC
Gate to Source Charge	Q_{GS}	V_{DD} = –24 V,		1.2		nC
Gate to Drain Charge	Q_{GD}	V_{GS} = –10 V		2.4		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = 5 A, V_{GS} = 0 V		0.96		V
Reverse Recovery Time	t_{rr}	I_F = 5 A, V_{GS} = 0 V,		37		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 50 A/μs		29		nC

Note Pulsed

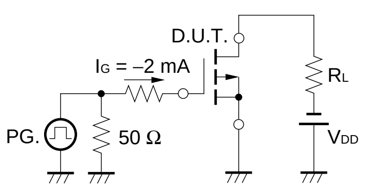
<R> **TEST CIRCUIT 1 AVALANCHE CAPABILITY**



TEST CIRCUIT 2 SWITCHING TIME



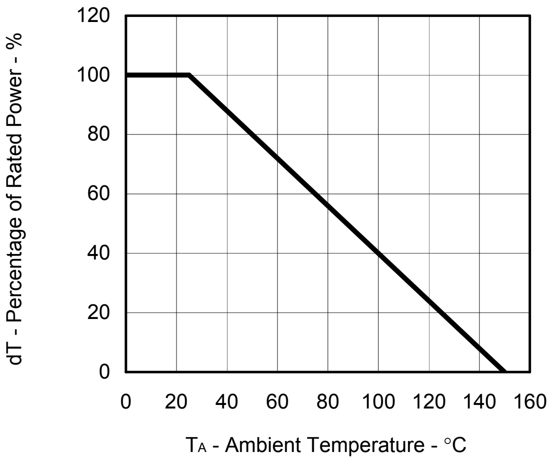
TEST CIRCUIT 3 GATE CHARGE



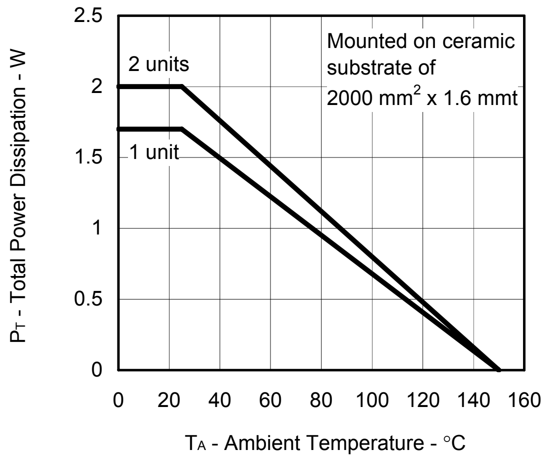
TYPICAL CHARACTERISTICS (T_A = 25°C)

(1) N-channel

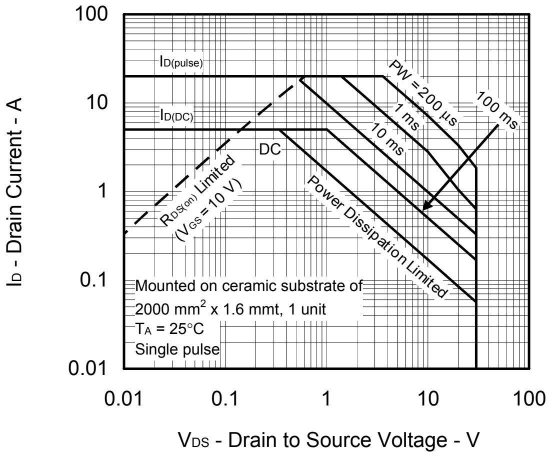
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



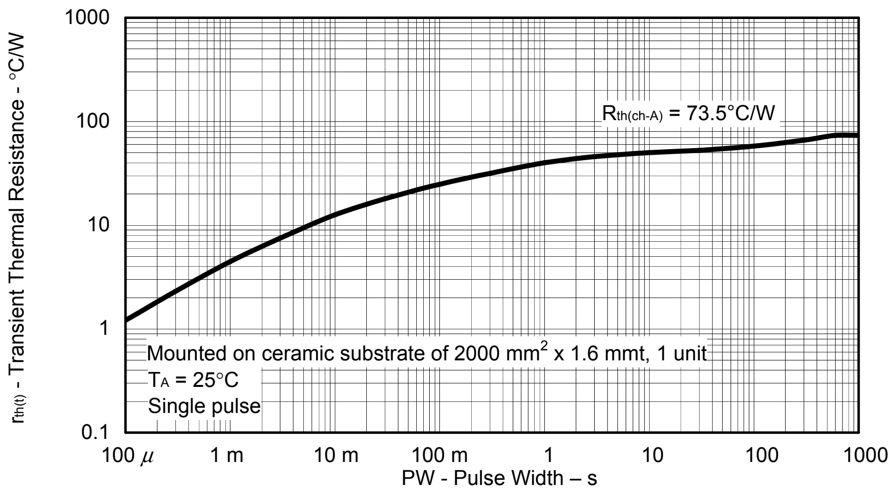
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



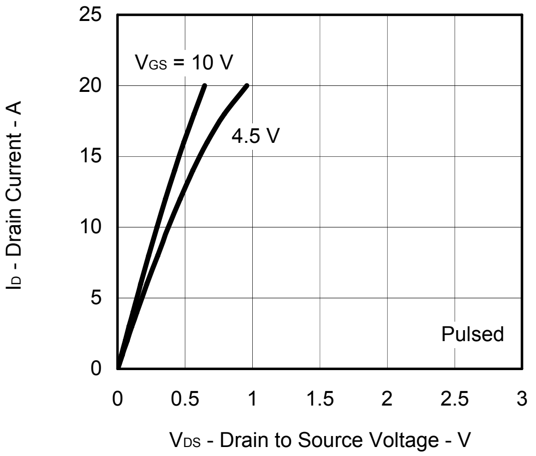
FORWARD BIAS SAFE OPERATING AREA



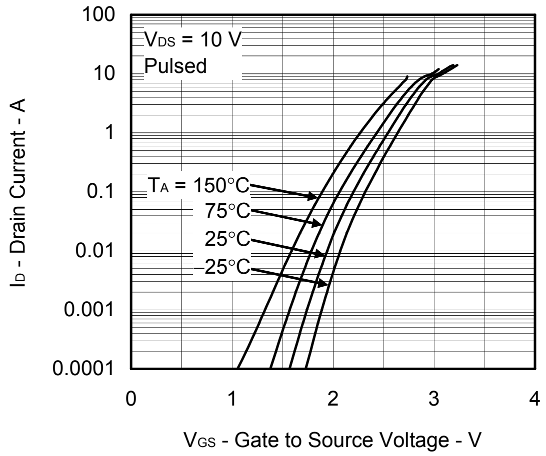
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



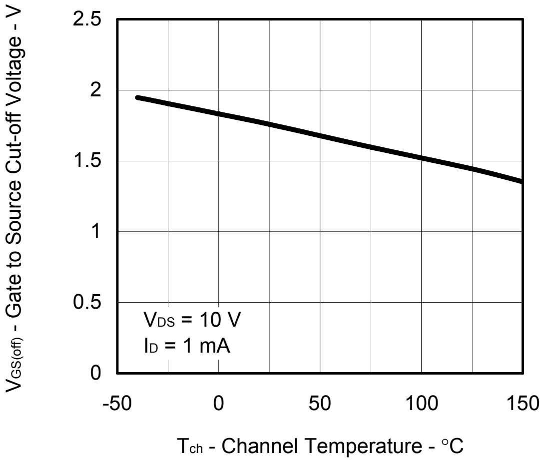
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



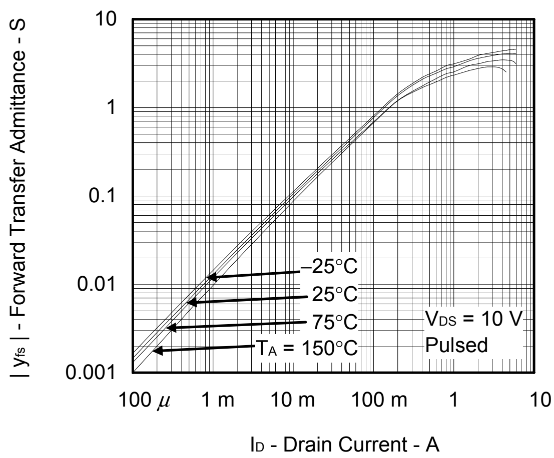
FORWARD TRANSFER CHARACTERISTICS



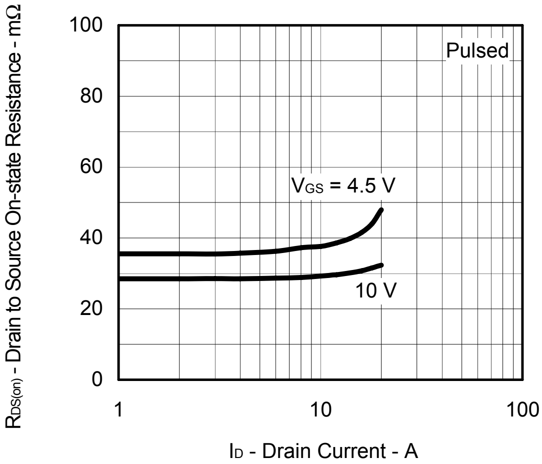
GATE TO SOURCE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



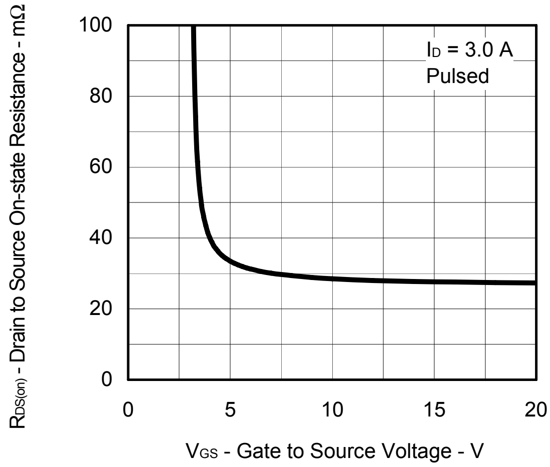
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



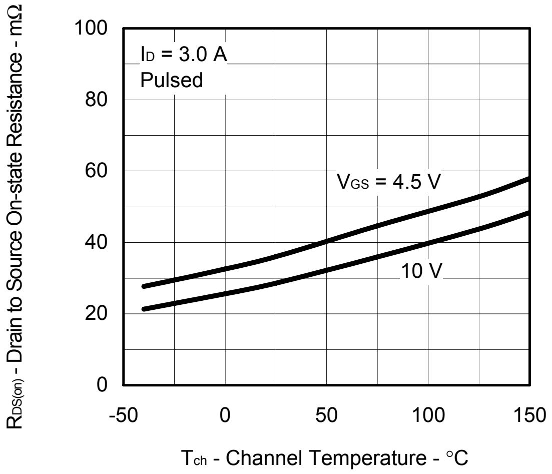
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



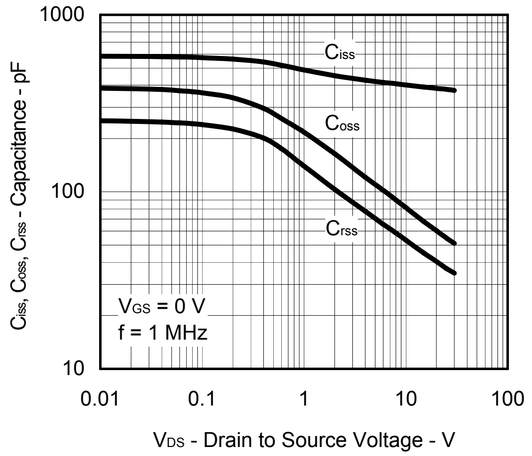
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



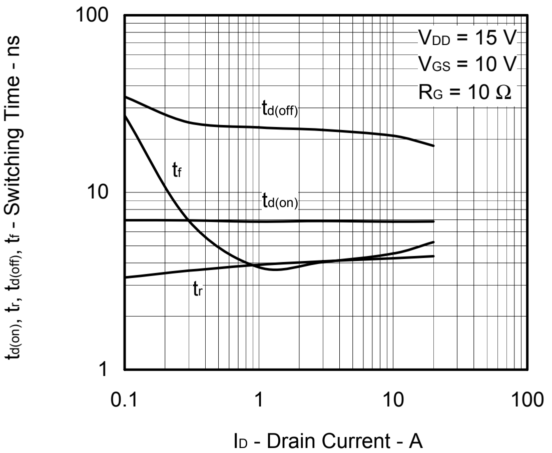
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



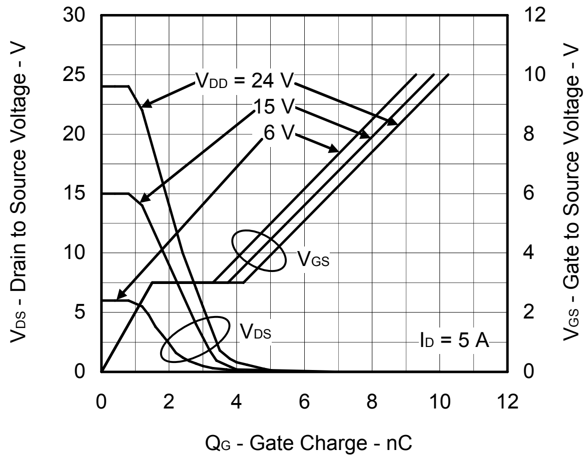
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



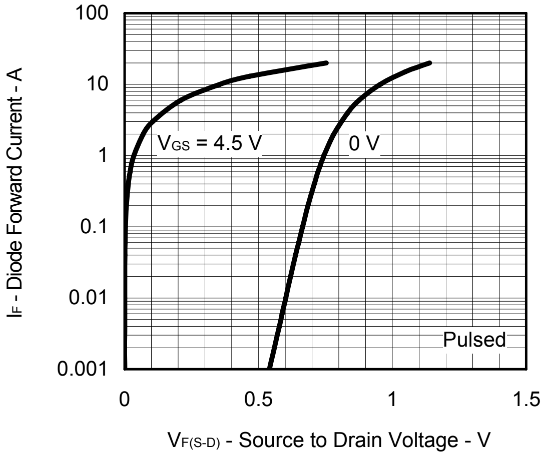
SWITCHING CHARACTERISTICS



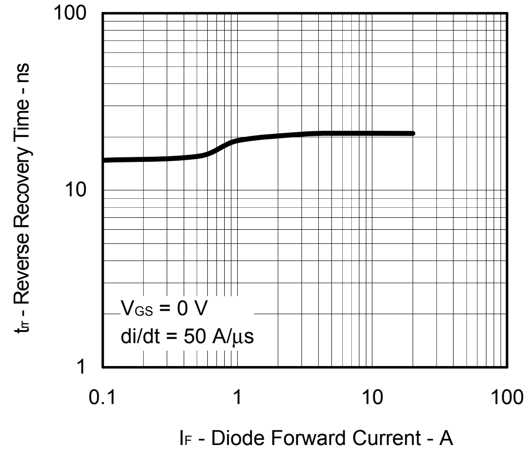
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

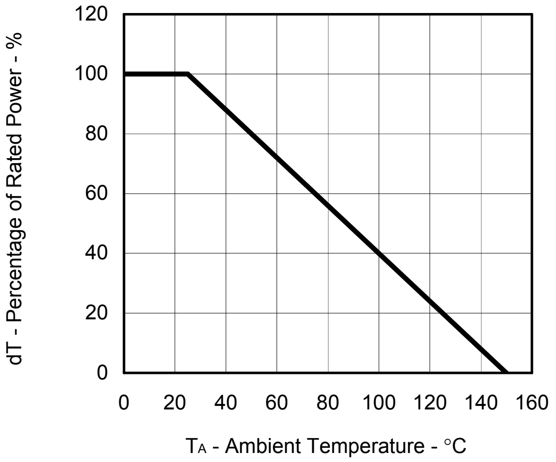


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

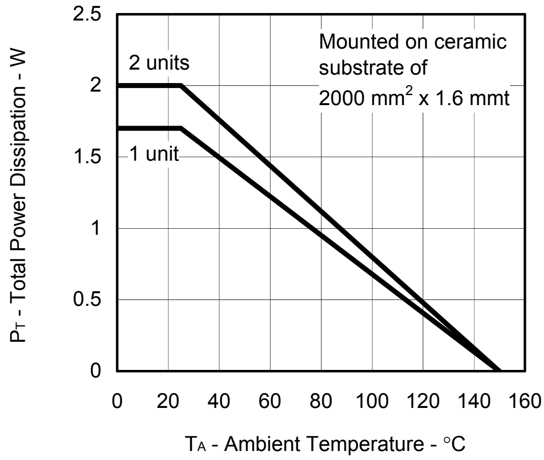


(2) P-channel

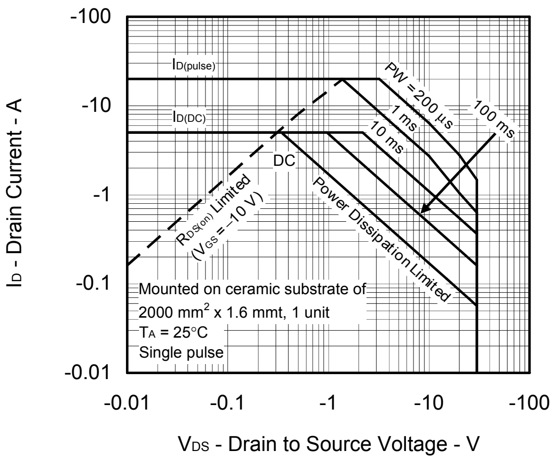
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



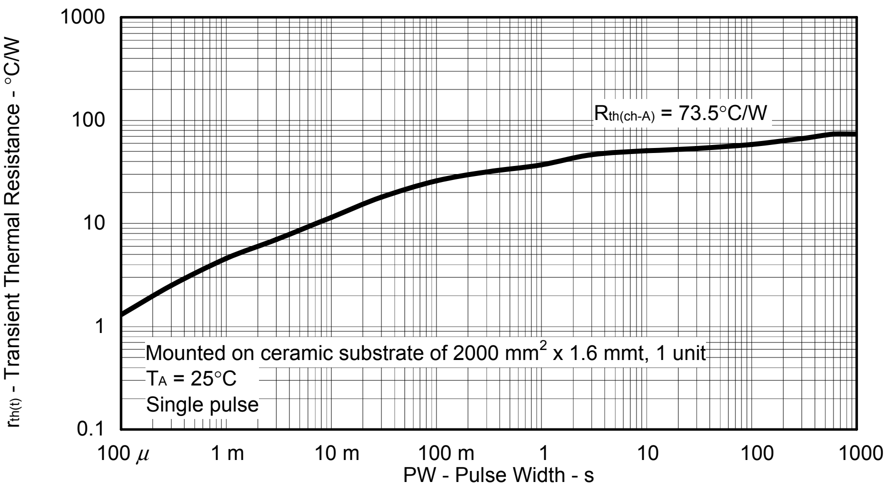
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



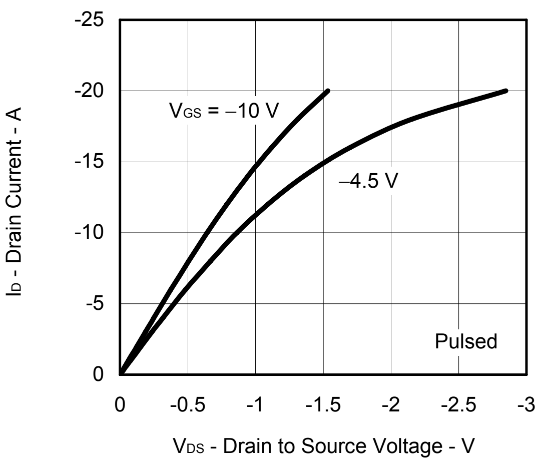
FORWARD BIAS SAFE OPERATING AREA



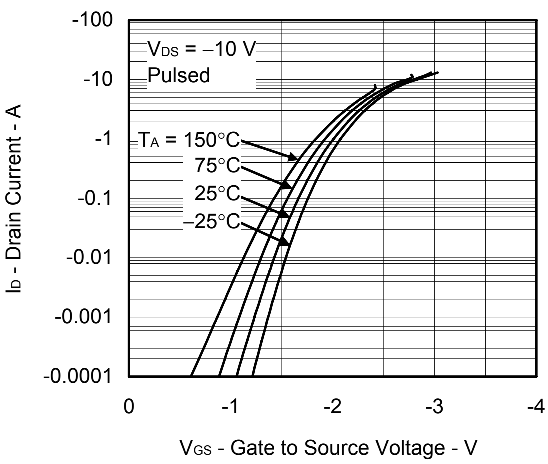
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



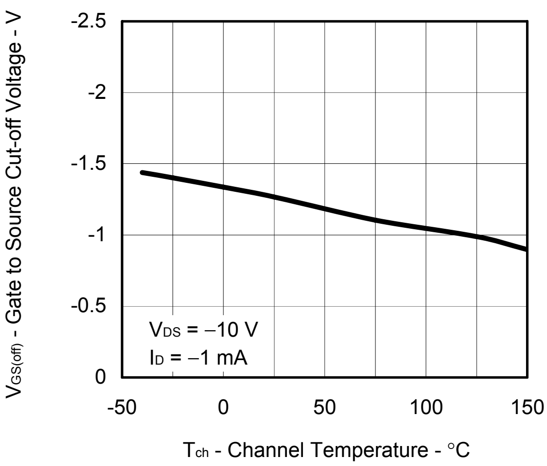
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



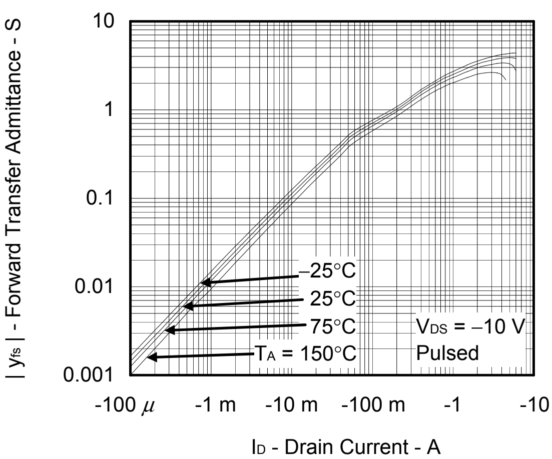
FORWARD TRANSFER CHARACTERISTICS



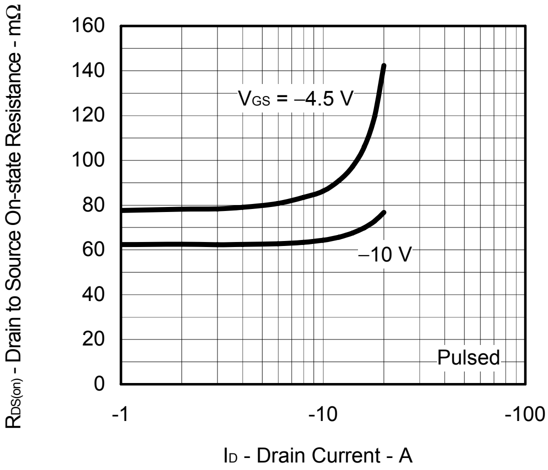
GATE TO SOURCE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



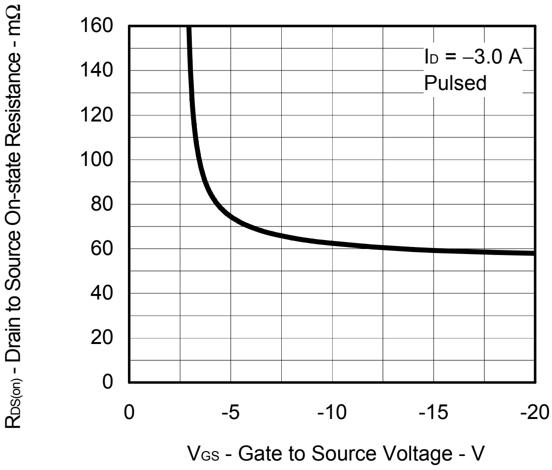
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



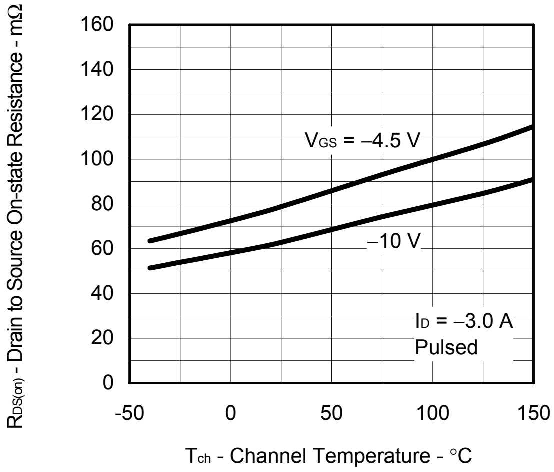
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



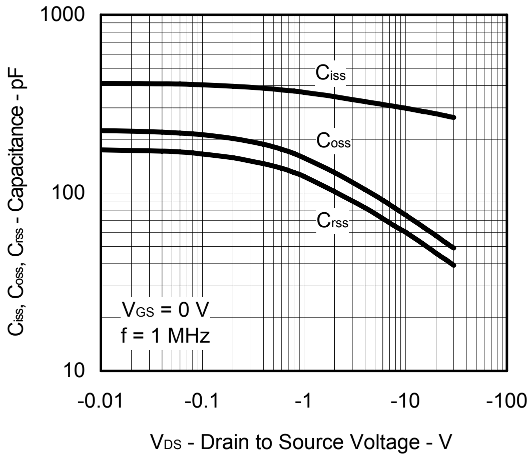
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



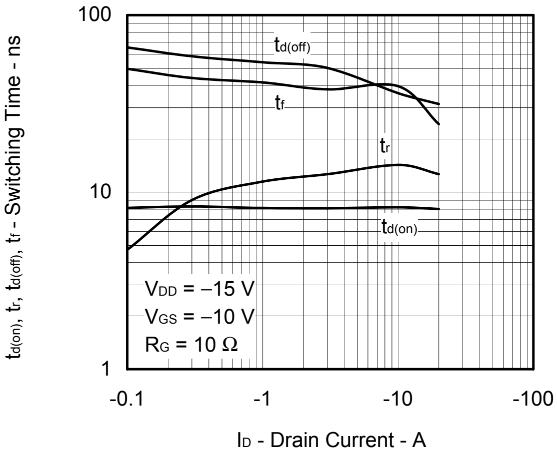
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



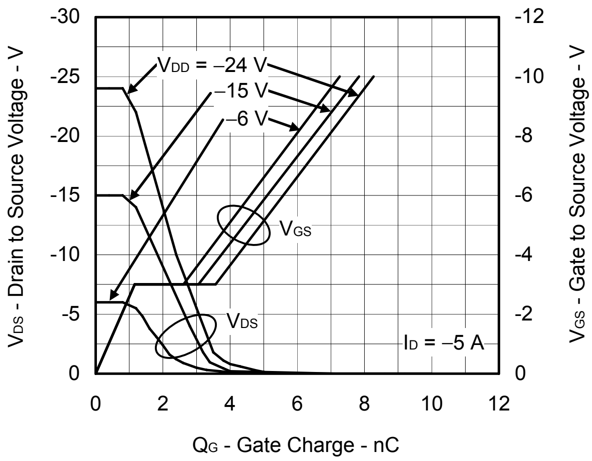
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



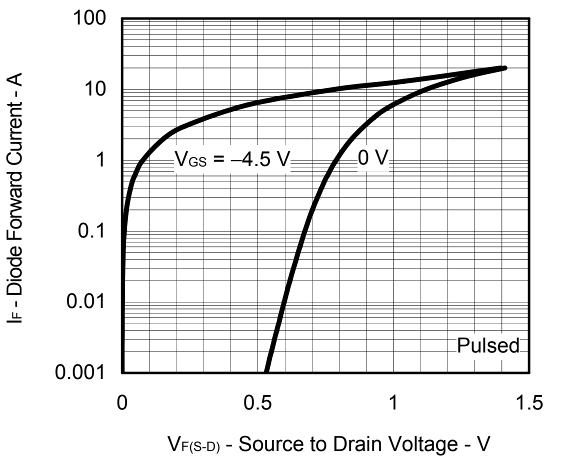
SWITCHING CHARACTERISTICS



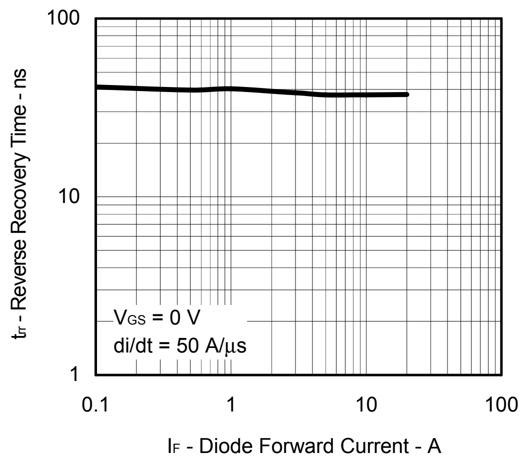
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

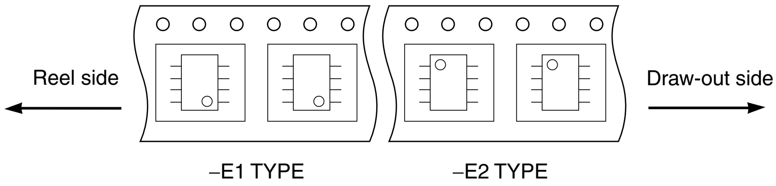


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

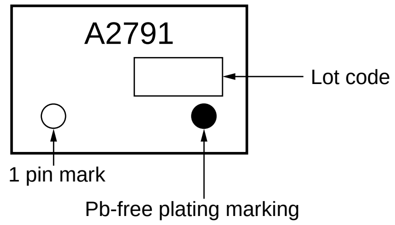


TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION



RECOMMENDED SOLDERING CONDITIONS

The μPA2791GR should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below Time at maximum temperature: 10 seconds or less Time of temperature higher than 220°C: 60 seconds or less Preheating time at 160 to 180°C: 60 to 120 seconds Maximum number of reflow processes: 3 times Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	IR60-00-3
Partial heating	Maximum temperature (Pin temperature): 350°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P350

Caution Do not use different soldering methods together (except for partial heating).

- **The information in this document is current as of November, 2007. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC Electronics data sheets or data books, etc., for the most up-to-date specifications of NEC Electronics products. Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.**
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